

2.7 V to 5.5 V Input, 3 A Single Synchronous Buck DC/DC Converter for Automotive

BD9S303MUF-C

General Description

BD9S303MUF-C is a synchronous buck DC/DC Converter with built-in low on-resistance power MOSFETs. It can provide current up to 3 A. Small inductor is applicable due to high switching frequency of 2.2 MHz. It is a current mode control and features fast transient response. The Light Load Mode control improves efficiency in light-load conditions. It is ideal for reducing standby power consumption of equipment. It has a built-in phase compensation circuit. Applications can be created with a few external components.

Features

- QuiCurTM
- Nano Pulse ControlTM
- AEC-Q100 Qualified(Note 1)
- Functional Safety Supportive Automotive Products

<u> √Nano</u>

- Single Synchronous Buck DC/DC Converter
- Adjustable Soft Start Function
- **Output Discharge Function**
- **Power Good Output**
- Input Under Voltage Lockout Protection (UVLO)
- Short Circuit Protection (SCP)
- Output Over Voltage Protection (OVP)
- Over Current Protection (OCP)
- Thermal Shutdown Protection (TSD)
- Light Load Mode (LLM)
- Selectable Spread Spectrum Function
- Wettable Flank QFN Package

(Note 1) Grade 1

Applications

- **Automotive Equipment**
- Other Electronic Equipment

Key Specifications

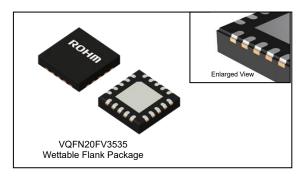
Input Voltage: 2.7 V to 5.5 V Output Voltage Setting: 0.6 V to V_{PVIN} x 0.75 V **Output Current:** 3 A (Max) 2.2 MHz (Typ) Switching Frequency: High Side FET ON Resistance: 65 mΩ (Typ) Low Side FET ON Resistance: 43 mΩ (Typ) Shutdown Circuit Current: 0 μA (Typ)

Operating Temperature:

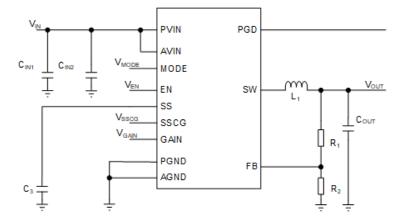
Package VQFN20FV3535

W (Typ) x D (Typ) x H (Max) 3.5 mm x 3.5 mm x 1.0 mm

-40 °C to +125 °C



Typical Application Circuit

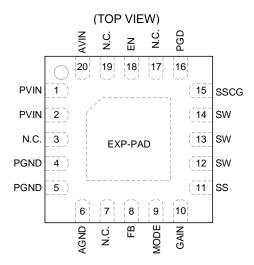


QuiCur[™], Nano Pulse Control[™] is a trademark or a registered trademark of ROHM Co., Ltd.

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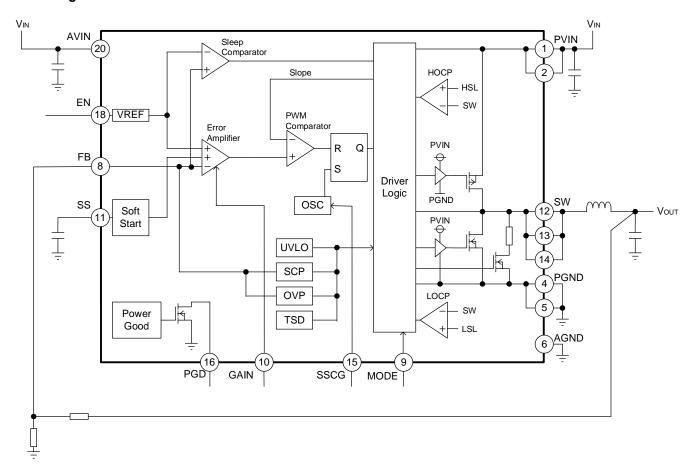
Pin Configuration



Pin Descriptions

escriptions		
Pin No.	Pin Name	Function
1, 2	PVIN	Power supply input pins that are used for the output stage of the switching regulator. Connect a ceramic capacitor of 10 μ F as a recommended value. For details, see Selection of Components Externally Connected 4. Selection of Input Capacitor.
3, 7, 17, 19	N.C.	This pin is not connected to the chip. Use this as open. If this pin is used other than open and adjacent pins are expected to be shorted, please confirm if there is any problem with the actual application.
4, 5	PGND	Ground pins for the output stage of the switching regulator.
6	AGND	Ground pin.
8	FB	V _{OUT} feedback pin. Connect output voltage divider to this pin to set the output voltage. For the output voltage setting method, see <u>Selection of Components Externally Connected 3. Output Voltage Setting.</u>
9	MODE	Pin for LLM control mode and Forced PWM (FPWM) mode. When this pin is set to High, the device is in the FPWM mode. When it is set to Low, it automatically transitions between LLM control mode and PWM control mode depending on the load current.
10	GAIN	This pin switches the gain of the internal error amplifier. When this pin is set to High, the device is in the fast load response mode, and when it is set to Low or open, the device is in the low output capacitance mode. For details, see Function Explanations Error Amplifier Gain Switching Function . This pin should be connected to AVIN (High) or AGND (Low).
11	SS	Pin for setting the soft start time. The rise time of the output voltage can be set by connecting a capacitor to this pin. See <u>Selection of Components Externally Connected 6.Selection of Soft Start Capacitor</u> for how to set the capacitance value.
12, 13, 14	SW	Switch pin. These pins are connected to the drain of the High Side FET and the Low Side FET.
15	SSCG	Pin to select Spread Spectrum function. Set High to enable Spread Spectrum and set Low to disable Spread Spectrum. This pin should be connected to AVIN (High) or AGND (Low).
16	PGD	Power Good pin, an open drain output. It needs to be pulled up to the power supply with a resistor. See <u>Function Explanations 3. Power Good Output</u> for setting the resistance.
18	EN	Device enable pin. Turning this pin Low forces the device to enter the shutdown mode. Turning this pin High makes the device to start up.
20	AVIN	Power supply input pin for internal circuit. This pin is shorted to the PVIN pin. Connect a ceramic capacitor of 0.1 μ F as a recommended value. For details, see <u>Selection of Components Externally Connected 4. Selection of Input Capacitor</u> .
-	EXP-PAD	A backside heat dissipation pad. Connecting to the internal PCB ground plane by using via provides excellent heat dissipation characteristics.

Block Diagram



Description of Blocks

1. VREF

The VREF block generates the internal reference voltage.

2. UVLO (Under Voltage Lockout)

The UVLO block is for under voltage lockout protection. It shuts down the device when the V_{AVIN} falls to 2.45 V (Typ) or lower. The threshold voltage has a hysteresis of 100 mV (Typ).

3. SCP (Short Circuit Protection)

This is the short circuit protection circuit. After soft start is judged to be completed, if the FB pin voltage falls to 0.42 V (Typ) or less and remain in that state for 1 ms (Typ), output MOSFETs turn OFF for 14 ms (Typ) and then restart the operation.

4. OVP (Over Voltage Protection)

This is the output over voltage protection circuit. When the FB pin voltage becomes V_{FB1} (0.6 V, Typ) +8 % or more, it turns the output MOSFETs OFF. After output voltage falls V_{FB1} +6 % or less, the output MOSFETs return to normal operation.

5. TSD (Thermal Shutdown)

This is the thermal shutdown circuit. It shuts down the device when the junction temperature (Tj) reaches to 175 °C (Typ) or more. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation with hysteresis of 25 °C (Typ).

6. HOCP (High Side Over Current Protection)

The Over Current Protection function operates by limiting the current that flows through High Side FET at each cycle of the switching frequency.

7. LOCP (Low Side Over Current Protection)

The Over Current Protection function operates by limiting the current that flows through Low Side FET at each cycle of the switching frequency.

8. Soft Start

The Soft Start circuit slows down the rise of output voltage during startup, which allows the prevention of output voltage overshoot. The soft start time can be specified by connecting a capacitor to the SS pin. See <u>Selection of Components</u> <u>Externally Connected 6. Selection of Soft Start Capacitor</u> for how to calculate the capacitance. A built-in soft start function is provided, and a soft start is initiated in tss (<u>Electrical Characteristics</u>) when the SS pin is open.

9. Error Amplifier

This block is an error amplifier with a reference voltage of 0.6 V (Typ) and FB pin voltage as inputs, and the gain setting can be switched between High and Low on the GAIN pin.

10.PWM Comparator

The PWM Comparator block compares the output voltage of the Error Amplifier and the Slope signal to determine the output switching pulse duty.

11.OSC (Oscillator)

This block generates the oscillating frequency.

12. Driver Logic

This block controls switching operation and various protection functions.

13. Power Good

When the FB pin voltage reaches V_{FB1} (0.6 V, Typ) within +6 % to -2 %, the built-in Nch MOSFET turns OFF and the PGD output turns High. There is a 2 % hysteresis on the threshold voltage, so the PGD output turns Low when the FB pin voltage reaches outside +8 % to -4 % of V_{FB1} .

14. Sleep Comparator

In LLM control mode, this block monitors the FB pin voltage. When the FB pin voltage reaches +1.5 % (Typ) or more of V_{FB1} (0.6 V, Typ), the device shifts to SLEEP state. This state is released when the FB pin voltage reaches +0.5 % (Typ) or less of V_{FB1} .

Absolute Maximum Ratings

Parameter	Symbol	Rating	Unit
Input Voltage	V _P VIN, V _A VIN	-0.3 to +7.0	V
EN Voltage	V _{EN}	-0.3 to V _{AVIN}	V
MODE, GAIN, SSCG Voltage	V _{MODE} , V _{GAIN} , V _{SSCG}	-0.3 to V _{AVIN}	٧
PGD Voltage	V_{PGD}	-0.3 to +7.0	V
FB, SS Voltage	V _{FB} , V _{SS}	-0.3 to V _{AVIN}	V
Maximum Junction Temperature	Tjmax	150	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Caution 1: Operating the IC over the absolute maximum ratings may damage the IC. The damage can either be a short circuit between pins or an open circuit between pins and the internal circuitry. Therefore, it is important to consider circuit protection measures, such as adding a fuse, in case the IC is operated over the absolute maximum ratings.

Caution 2: Should by any chance the maximum junction temperature rating be exceeded the rise in temperature of the chip may result in deterioration of the properties of the chip. In case of exceeding this absolute maximum rating, design a PCB with thermal resistance taken into consideration by increasing board size and copper area so as not to exceed the maximum junction temperature rating.

Thermal Resistance^(Note 1)

Parameter		Thermal Res	1.1:4	
		1s ^(Note 3)	2s2p ^(Note 4)	Unit
VQFN20FV3535				
Junction to Ambient	θја	147.6	44.8	°C/W
Junction to Top Characterization Parameter ^(Note 2)	Ψ_{JT}	26.0	16.0	°C/W

(Note 1) Based on JESD51-2A (Still-Air)

(Note 2) The thermal characterization parameter to report the difference between junction temperature and the temperature at the top center of the outside surface of the component package.

(Note 3) Using a PCB board based on JESD51-3. (Note 4) Using a PCB board based on JESD51-5. 7

(Note 4) Using a FCD board based t	<i>III</i> JESDS 1-5, 7.	·
Layer Number of Measurement Board	Material	Board Size
Single	FR-4	114.3 mm x 76.2 mm x 1.57 mmt
Тор		
Copper Pattern	Thickness	
Footprints and Traces	70 um	

Layer Number of	Material	Board Size		Therma	ıl Via ^{(/}	lote 5)
Measurement Board	Material	Dualu Size	Pitch	Di	ameter	
4 Layers	FR-4	114.3 mm x 76.2 mm	1.20 mm	Ф0).30 mm	
Тор		2 Internal Lay	2 Internal Layers		ottom	
Copper Pattern	Thickness	Copper Pattern Thickness		Copper Pattern		Thickness
Footprints and Traces	70 µm	74.2 mm x 74.2 mm 35 µm 7		74.2 mm x 74.2 mm		70 µm

(Note 5) This thermal via connect with the copper pattern of layers 1,2, and 4. The placement and dimensions obey a land pattern.

Recommended Operating Conditions

giiiii g g g g g g g g g g g g g g g g				
Parameter	Symbol	Min	Max	Unit
Input Voltage	V _{PVIN} , V _{AVIN}	2.7	5.5	V
Operating Temperature	Та	-40	+125	°C
Output Current	l _{out}	-	3	Α
Output Voltage Setting	Vout	0.6 ^(Note 1)	V _{PVIN} x 0.75	V
SW Minimum ON Time	ton_min	-	50	ns

(Note 1) Although the output voltage is configurable at 0.6 V and higher, it may be limited by the SW min ON pulse width. For the configurable range, refer to the Output Voltage Setting in Selection of Components Externally Connected.

Electrical Characteristics

(Unless otherwise specified Ta = Tj = -40 °C to +150 °C, $V_{AVIN} = V_{PVIN} = 5.0 \text{ V}$, $V_{EN} = 5.0 \text{ V}$, Typical value is Tj = +25 °C)

ss otherwise specified Ta = Tj = -40 °C Parameter	Symbol	Min	Тур	Max	Unit	Conditions
AVIN	,		31			
Shutdown Circuit Current	I _{SDN}	_	0	10	μA	V _{EN} = 0 V, Tj = 25 °C
Circuit Current	Icc	-	22	30	μA	$V_{MODE} = 0 V$, $I_{OUT} = 0 mA$,
UVLO Detection Voltage	V _{UVLO1}	2.30	2.45	2.60	V	Tj = 25 °C, No switching V _{AVIN} Falling
UVLO Release Voltage	V _{UVLO2}	2.40	2.45	2.70	V	V _{AVIN} Rising
UVLO Hysteresis Voltage	Vuvlo-HYS	50	100	125	mV	Tj = 25 °C
ENABLE	V UVLO-HYS	30	100	125	IIIV	1] - 23 0
EN Input Voltage High	V _{ENH}	1.0	-	V _{AVIN}	V	
EN Input Voltage Low	VENH	GND	_	0.4	V	
EN Input Current	I _{EN}	2	4	6	μA	V _{EN} = 5 V, Tj = 25 °C
MODE, GAIN, SSCG	IEN		-	U	μ/ι	VEN - 0 V, 1j - 20 0
MODE Input Voltage High	Vмоден	1.5	-	V _{AVIN}	V	
MODE Input Voltage Low	VMODEL	GND	-	0.4	V	
MODE Input Current	I _{MODE}	6	11	16	μA	V _{MODE} = 5 V, Tj = 25 °C
GAIN Input Voltage High	VGAINH	1.5	11	V _{AVIN}	V	V MODE - 3 V, 1 J - 23 C
GAIN Input Voltage Low	VGAINH	GND	-	0.4	V	
GAIN Input Current		6	11	16	-	V _{GAIN} = 5 V, Tj = 25 °C
SSCG Input Voltage High	IGAIN	1.5	11	V _{AVIN}	μA V	VGAIN - 5 V, 1] - 25 C
SSCG Input Voltage Low	Vsscgh		-	0.4	V	
SSCG Input Current	V _{SSCGL}	GND	- 11			V ₂₂₂₂ = 5 \/ Ti = 25 °C
•	Isscg	6	11	16	μA	V _{SSCG} = 5 V, Tj = 25 °C
Reference Voltage, Error Amplifier	V _{FB1}	0.501	0.600	0.600	V	PWM Mode
FB Pin Voltage Light Load Detection Voltage	V _{FB1}	0.591	0.600 0.609	0.609 0.620	V	V _{FB} Rising, V _{MODE} = 0 V
FB Input Current			0.009	+0.1		V _{FB} = 0.6 V, Tj = 25 °C
Soft Start	I _{FB}	-0.1	U	₹0.1	μA	VFB = 0.0 V, 1j = 25 C
EN Waiting Time	t	150	450	750	ше	
Soft Start Time	twait		0.80	1.00	μs	V _{AVIN} = 5 V, SS Pin OPEN
	tss	0.60 -1.4	-1.0	-0.6	ms	VAVIN - 5 V, 35 PIII OPEN
SS Charge Current	Iss	-1.4	-1.0	-0.0	μA	
Switching Frequency Switching Frequency	fsw	2.0	2.2	2.4	MHz	V _{SSCG} = 0 V
Switching Frequency	f _{SWSSCG}	1.90	-	2.52	MHz	V _{SSCG} = 5 V
(Spread Spectrum) Spread Spectrum Modulation Rate	Δfsscg	_	4.5	_	%	V _{SSCG} = 5 V
Spread Spectrum Modulation Cycle	tsscg_cycle	380	466	560	μs	Vsscg = 5 V
Power Good	1330G_CTOLL	000	100	000	μο	V3303 V
PGD Falling (Fault) Voltage	V _{PGDTH_FF}	V _{FB1} x 0.95	V _{FB1}	V _{FB1} x 0.97	V	V _{FB} Falling
PGD Rising (Good) Voltage	V _{PGDTH_RG}	V _{FB1} x 0.97	x 0.96 V _{FB1} x 0.98	V _{FB1} x 0.99	V	V _{FB} Rising
PGD Rising (Fault) Voltage	V _{PGDTH_RF}	V _{FB1} x 1.07	V _{FB1} x 1.08	V _{FB1} x 1.09	V	V _{FB} Rising
PGD Falling (Good) Voltage	V _{PGDTH_FG}	V _{FB1} x 1.05	V _{FB1} x 1.06	V _{FB1} x 1.07	V	V _{FB} Falling
PGD Falling (Fault) Detection Delay	tpgdelff	60	105	150	μs	
PGD Rising (Fault) Detection Delay	tpgdelrf	60	105	150	μs	
PGD Output Leakage Current	I _{LEAKPGD}	-	0	2	μA	V _{PGD} = 5 V, Tj = 25 °C
PGD FET ON Resistance	R _{PGD}	20	50	80	Ω	
PGD Output Low Level Voltage	V _{PGDL}	0.02	0.05	0.08	V	I _{PGD} = 1 mA

Electrical Characteristics – continued (Unless otherwise specified Ta = Tj = -40 °C to +150 °C, V_{AVIN} = V_{PVIN} = 5.0 V, V_{EN} = 5.0 V, Typical value is Tj = +25 °C)

Parameter	Symbol	Min	Тур	Max	Unit	Conditions
Switch MOSFET						
High Cids FFT ON Designation		18	65	112	mΩ	V _{PVIN} = 5 V
High Side FET ON Resistance	Ronh	27	70	120	mΩ	V _{PVIN} = 3.3 V
Law Sida FFT ON Decistores	Б	14	43	72	mΩ	V _{PVIN} = 5 V
Low Side FET ON Resistance	Ronl	16	48	80	mΩ	V _{PVIN} = 3.3 V
High Side FET Leakage Current	ILEAKSWH	-	0	15	μA	V _{PVIN} = 5.5 V, V _{SW} = 0 V Tj = 25 °C
Low Side FET Leakage Current	ILEAKSWL	-	0	5	μA	V _{PVIN} = 5.5 V, V _{SW} = 5.5 V Tj = 25 °C
High Side FET Current Limit ^(Note 1)	Іосрн	3.6	5.4	7.2	Α	
Low Side FET Current Limit ^(Note 1)	IOCPL	3.0	4.4	6.0	А	
SW Discharge Resistance	R _{DIS}	30	60	100	Ω	V _{EN} = 0 V, V _{SW} = 3.3 V
SCP, OVP	1		I	I.	1	
Short Circuit Protection Detection Voltage	Vscp	0.34	0.42	0.50	V	V _{FB} Falling
Output Over Voltage Protection Detection Voltage	V _{OVP}	V _{FB1} x 1.07	V _{FB1} x 1.08	V _{FB1} x 1.09	V	V _{FB} Rising

(Note 1) This is design value. Not production tested.

Typical Performance Curves (Reference Data)

Unless otherwise specified $V_{IN} = V_{EN}$

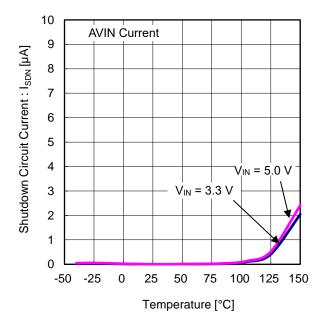


Figure 1. Shutdown Circuit Current vs Temperature

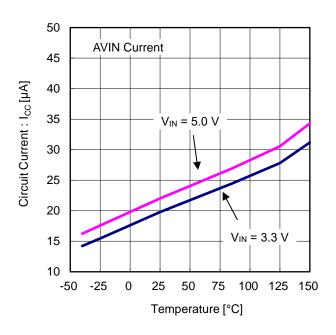


Figure 2. Circuit Current vs Temperature

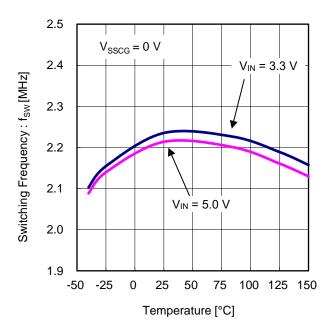


Figure 3. Switching Frequency vs Temperature

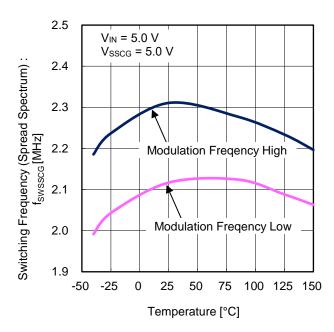


Figure 4. Switching Frequency (Spread Spectrum) vs Temperature

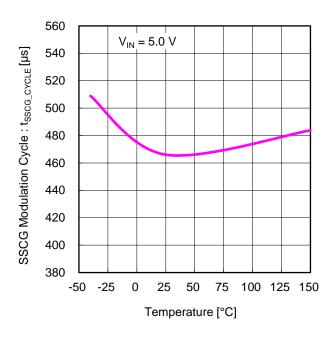


Figure 5. SSCG Modulation Cycle vs Temperature

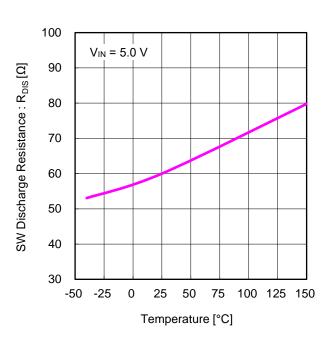


Figure 6. SW Discharge Resistance vs Temperature

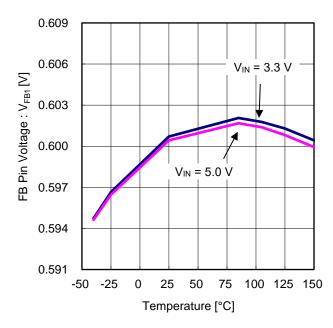


Figure 7. FB Pin Voltage vs Temperature

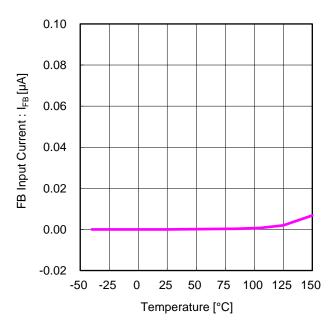


Figure 8. FB Input Current vs Temperature

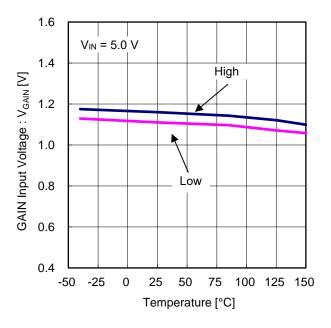


Figure 9. GAIN Input Voltage vs Temperature

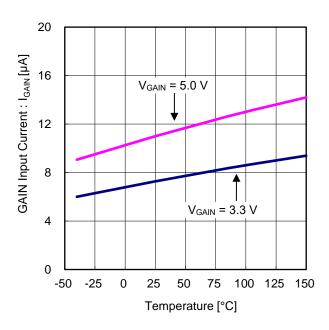


Figure 10. GAIN Input Current vs Temperature

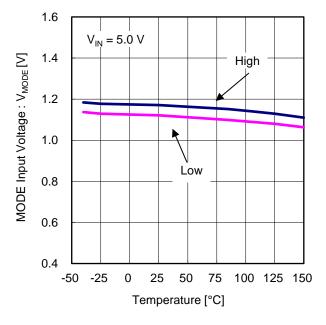


Figure 11. MODE Input Voltage vs Temperature

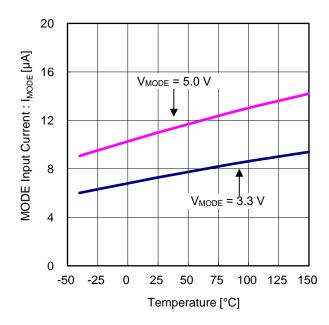


Figure 12. MODE Input Current vs Temperature

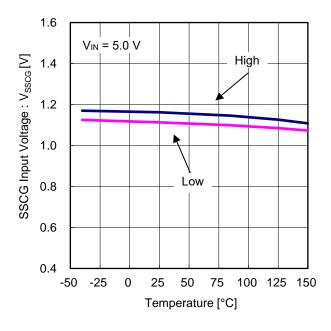


Figure 13. SSCG Input Voltage vs Temperature

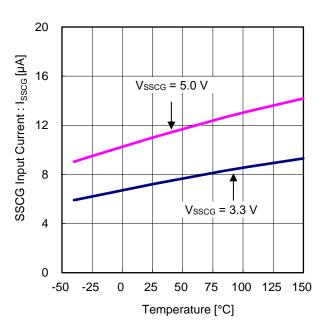


Figure 14. SSCG Input Current vs Temperature

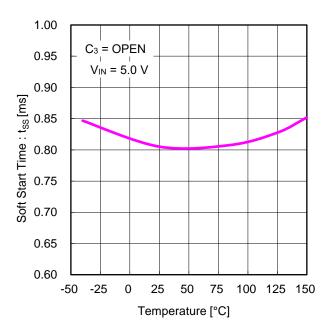


Figure 15. Soft Start Time vs Temperature

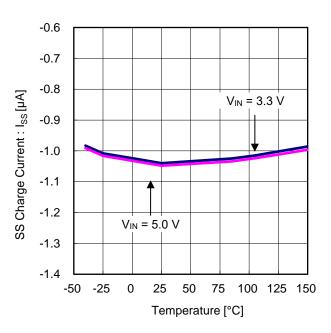


Figure 16. SS Charge Current vs Temperature

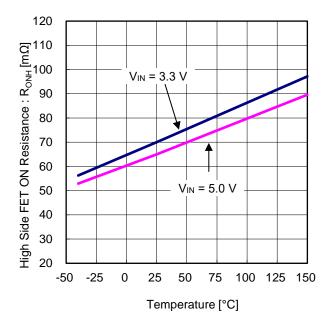


Figure 17. High Side FET ON Resistance vs Temperature

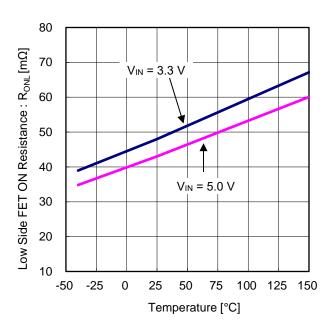


Figure 18. Low Side FET ON Resistance vs Temperature

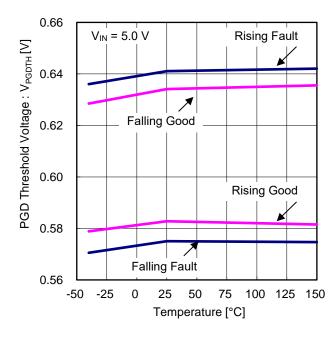


Figure 19. PGD Threshold Voltage vs Temperature

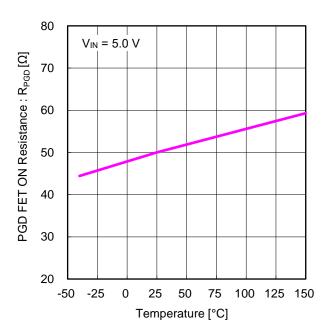


Figure 20. PGD FET ON Resistance vs Temperature

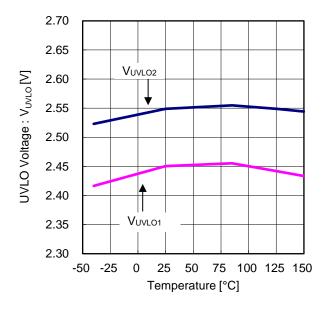


Figure 21. UVLO Voltage vs Temperature

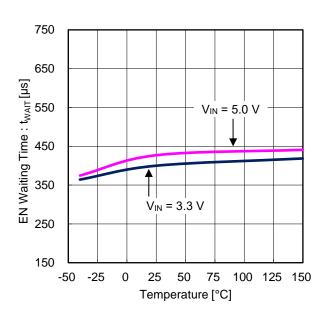


Figure 22. EN Waiting Time vs Temperature

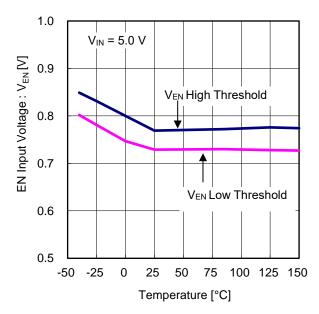


Figure 23. EN Input Voltage vs Temperature

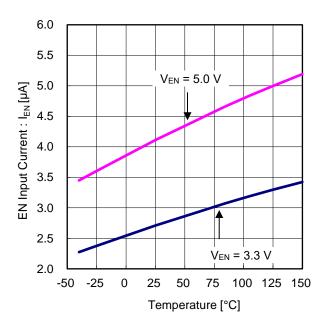


Figure 24. EN Input Current vs Temperature

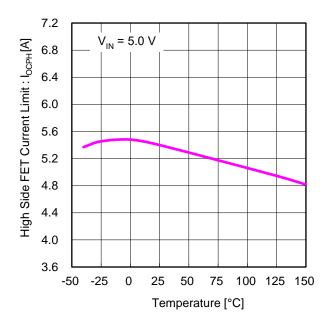


Figure 25. High Side FET Current Limit vs Temperature

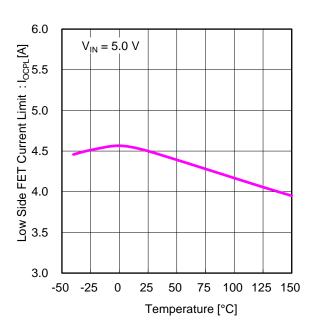


Figure 26. Low Side FET Current Limit vs Temperature

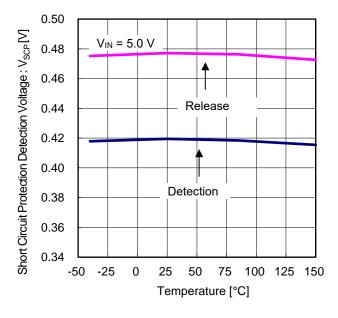


Figure 27. Short Circuit Protection Detection Voltage vs Temperature

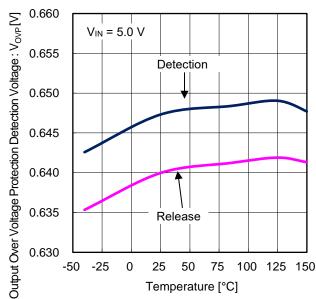


Figure 28. Output Over Voltage Protection Detection Voltage vs Temperature

Function Explanations

1. Enable Control

The device shutdown can be controlled by the voltage applied to the EN pin. When EN voltage V_{EN} becomes V_{ENH} (1.0 V) or more, the internal circuit is activated, and the device starts up with soft start. The delay time t_{WAIT} (450 μ s, Typ) is implemented from the EN pin becoming high to V_{OUT} starting up. When the SS pin is open, the device starts with the built-in soft start time t_{SS} (0.8 ms, Typ). When V_{EN} becomes V_{ENL} (0.4 V) or less, the device is shutdown. During shutdown, the SW pin is pulled down with resistance R_{DIS} (60 Ω , Typ) to discharge the output voltage.

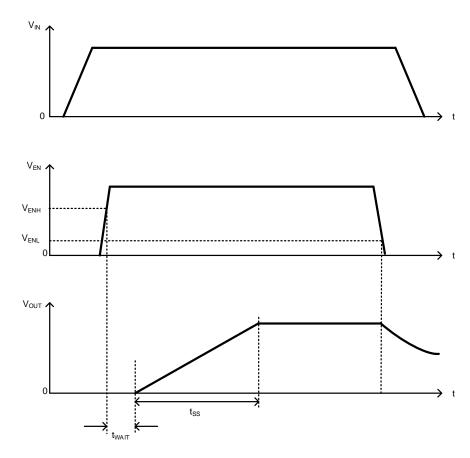


Figure 29. Enable ON/OFF Timing Chart

2. Nano Pulse Control™

Nano Pulse ControlTM is an original technology developed by ROHM Co., Ltd. It enables to control voltage stably, which is difficult in the conventional technology, even in a narrow SW ON time such as less than 50 ns at typical condition. Narrow SW ON Pulse enables direct convert of high input voltage to low output voltage. The output voltage V_{OUT} 0.8 V or less can be output directly from the supply voltage V_{IN} 5.0 V at 2.2 MHz.

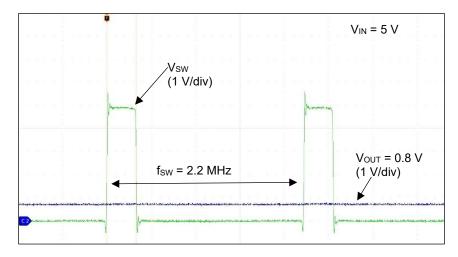


Figure 30. Switching Waveform ($V_{IN} = 5.0 \text{ V}$, $V_{OUT} = 0.8 \text{ V}$, $I_{OUT} = 1.0 \text{ A}$, $f_{SW} = 2.2 \text{ MHz}$)

Function Explanations - continued

3. Power Good Output

When the FB pin voltage becomes within 0.6 V (Typ) -2 %, the open drain output MOSFET of the PGD pin turns off and the PGD pin output becomes High by the pull-up resistor. When the FB pin voltage is out of the range of 0.6 V (Typ) -4 % and the condition continues for $t_{PGDELFF}$ (105 μ s, Typ), the open drain output MOSFET of the PGD pin turns on and the PGD pin is pulled down with an impedance of 50 Ω (Typ). When the FB pin voltage is out of the range of 0.6 V (Typ) -4 % and the time until the voltage returns to within -2 % is shorter than $t_{PGDELFF}$, the PGD state is maintained High.

Also Power Good function operate when the IC detects Output Over Voltage. If the FB pin voltage is outside the range of 0.6 V (Typ) +8 % and the condition continues for $t_{PGDELRF}$ (105 μ s, Typ) time, the open drain output MOSFET of the PGD pin turns on and the PGD pin is pulled down with an impedance of 50 Ω (Typ). When the FB pin voltage becomes within 0.6 V (Typ) +6 %, the open drain output MOSFET of PGD pin turns off and the output becomes High. It is recommended that the PGD pin be pulled up to the power supply with a resistor from 2 $k\Omega$ to 100 $k\Omega$.

If the power good function is not used, connect the PGD pin to OPEN or GND.

During shutdown, the PGD pin is pulled down if V_{AVIN} is 1.2 V or more.

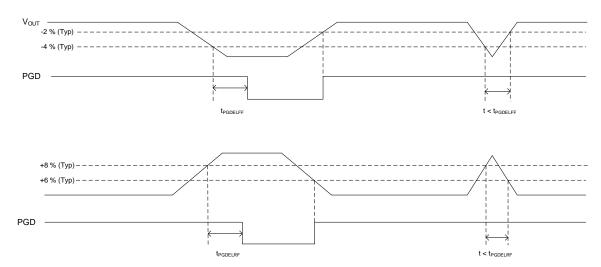


Figure 31. Power Good Timing Chart

4. Output Discharge Function

When even one of the following conditions is satisfied, output is discharged with 60 Ω (Typ) resistance through the SW pin.

- V_{EN} becomes 0.4 V or less
- V_{AVIN} becomes 2.45 V (Typ) or less (UVLO)
- V_{FB} becomes 0.42 V (Typ) or less and remains there for 1 ms (Typ) (SCP)
- V_{FB} becomes V_{FB1} (0.6 V, Typ) +8 % or more (OVP)
- Tj becomes 175 °C (Typ) or more (TSD)

When all the above conditions are released, output discharge is stopped.

5. QuiCur™

QuiCur™ is a combination of technologies that provides fast load response.

This technology reduces the amount of output voltage change in response to transient changes in load current. It also reduces the capacitance of output capacitors required for power supply ICs, thereby reducing the number of components and the board mounting area.

6. Error Amplifier Gain Switching Function

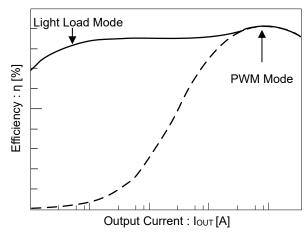
The gain of the error amplifier in the device can be switched by the GAIN pin; connecting the GAIN pin to the AVIN pin sets the device in the fast load response mode, in which the error amplifier gain is set high, to suppress output voltage changes during load transients. At this time, connect an output capacitor C_{OUT} of 44 μ F (Typ) or more.

When the GAIN pin is connected to the AGND pin or left open, the error amplifier gain is set to low, and the mode becomes the low output capacitance mode that operates stably even when C_{OUT} is 22 μF (Typ). However, the output voltage change during load transients will be larger than in the fast load response mode. Do not switch the GAIN pin connection during operation.

Function Explanations - continued

7. Light Load Mode Control and Forced PWM Mode Control

BD9S303MUF-C is a synchronous DC/DC converter with integrated POWER MOSFETs and realizes high transient response by using current mode Pulse Width Modulation (PWM) mode control architecture. Under a heavy load, the switching operation is performed with the PWM mode control at a fixed frequency. When the load is lighter, the operation is changed over to the Light Load Mode (LLM) control to improve the efficiency.



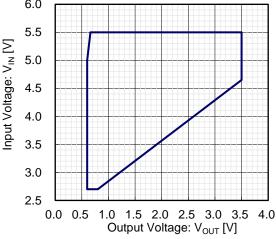


Figure 32. Efficiency (Light Load Mode, PWM Mode)

Figure 33. Recommended Condition for LLM

When the MODE pin is Low, the Light Load Mode is enabled. At light loads the output voltage rises by supplying energy to the load side, and it is changed to SLEEP state when the output voltage exceeds to V_{FB2} (101.5 % of its setting voltage V_{FB1}). During SLEEP state, switching operation is stopped and the circuit current is reduced by stopping the circuit operation except for the circuit of output voltage monitor. Then, the switching operation restarts when the output voltage decreases less than V_{FB3} (100.5 % of V_{FB1}) by the load current.

If the light load mode operation is not required, the IC operates in Forced PWM mode by applying high voltage to the MODE pin. In Forced PWM mode, the IC operates with fixed frequency regardless of the output load and the output ripple voltage can be reduced. Also, during soft start time, the IC operates in Forced PWM mode regardless of the condition of the MODE pin. After 1.5 times the soft start time, the control mode changes according to the MODE pin condition. In addition, good EMI performance in AM band may not be provided by a load condition in LLM. To avoid this, use Forced PWM mode. It is recommended to use the forced PWM mode in heavy load conditions by dynamically changing the MODE pin from Low to High depending on the output load.

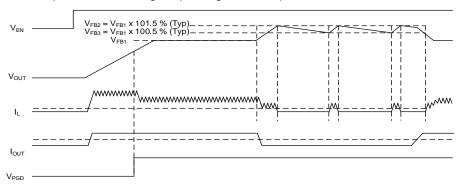


Figure 34. Timing Chart in Light Load Mode (MODE = Low)

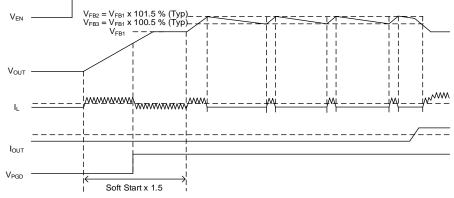


Figure 35. Timing Chart in Light Load Mode after Soft Start Time (MODE = Low)

Function Explanations - continued

8. Spread Spectrum Function

Connecting the SSCG pin with the AVIN pin activates the Spread Spectrum function, reducing the EMI noise level. When the Spread Spectrum function is activated, the switching frequency is varied with triangular wave of $\Delta f_{\rm SSCG}$ (±4.5 %, Typ) amplitude centered on typical frequency $f_{\rm SW}$ (2.2 MHz, Typ). The period of the triangular wave is $t_{\rm SSCG_CYCLE}$ (466 μ s, Typ). However, this function is masked until 1.5 times the soft start time has elapsed after the output starts. Connecting the SSCG pin with GND deactivates this function. After enabling the device with the SSCG pin connected to either AVIN pin or AGND pin, it is prohibited to change the SSCG pin connection.

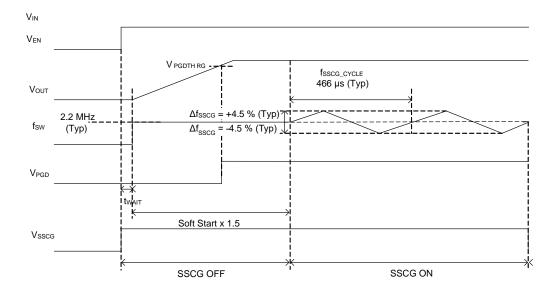


Figure 36. Spread Spectrum Function Timing Chart

Protection Function

1. Short Circuit Protection (SCP)

When the FB pin voltage has fallen to 0.42 V (Typ) or less and remained there for 1 ms (Typ), the device stops the switching operation for 14 ms (Typ) and subsequently initiates a restart due to the Short Circuit Protection. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the device should not be used in applications characterized by continuous operation of the protection circuit (e.g. when a load that significantly exceeds the output current capability of the chip is connected at all times).

EN Pin	FB Pin	Short Circuit Protection	Short Circuit Protection Operation
1.0.\/ or more	≤ 0.42 V (Typ)	Enabled	ON
1.0 V or more	≥ 0.48 V (Typ)	Enabled	OFF
0.4 V or less	-	Disabled	OFF

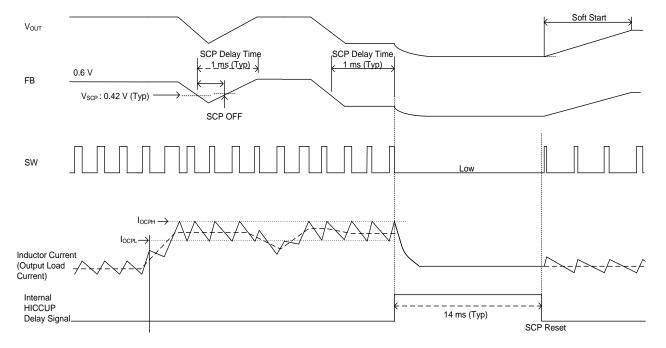


Figure 37. Short Circuit Protection (SCP) Timing Chart

2. Over Current Protection (OCP)

The over current protection function limits the current flowing to the High Side FET and Low Side FET. When the current flowing to the High Side FET reaches Iocph, the High Side FET is turned off and the peak current limit is applied. Next, when the Low Side FET is turned on, the current flowing to the Low Side FET is monitored and if it is larger than Iocpl, the turn-on operation is skipped due to the current limit of the Low Side FET.

As the Low Side FET ON state continues, the inductor current decreases, and when it becomes locpl or less, the current limit is released, and SW turns ON by the next set signal inside the device. This series of operations provides over current protection. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the device should not be used in applications characterized by continuous operation of the protection circuit (e.g. when a load that significantly exceeds the output current capability of the chip is connected at all times).

Protection Function – continued

3. Under Voltage Lockout Protection (UVLO)

It shuts down the device when the AVIN pin voltage falls to 2.45 V (Typ) or less. The threshold voltage has a hysteresis of 100 mV (Typ).

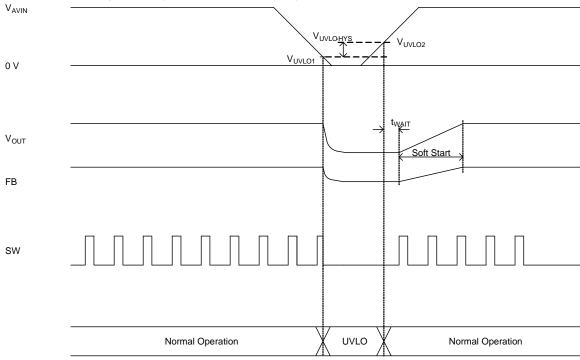


Figure 38. Under Voltage Lockout Protection (UVLO) Timing Chart

4. Thermal Shutdown (TSD)

This is the thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. However, if the rating is exceeded for a continued period and the junction temperature (Tj) rises to 175 °C (Typ), the TSD circuit activates and the output MOSFETs turn OFF. When the Tj falls below the threshold, the circuits are automatically restored to normal operation. Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

5. Over Voltage Protection (OVP)

The device incorporates an over voltage protection circuit to minimize the output voltage overshoot when recovering from fast load transients or output fault conditions. If the FB pin voltage becomes Output Over Voltage Protection detection voltage V_{FB1} + 8 % or more, the MOSFETs on the output stage are turned OFF to prevent the increase in the output voltage. After detection, switching operation is restarted if the output decreases and the over voltage state is released. Output Over Voltage Protection detection voltage and release voltage have a hysteresis of 2 %.

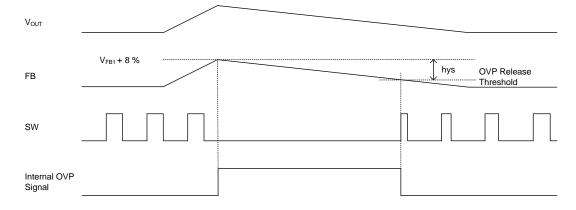


Figure 39. Over Voltage Protection (OVP) Timing Chart

Selection of Components Externally Connected

Necessary parameters in designing the power supply are as follows:

Table 1. Application Specification

Parameter	Symbol	Example Value
Input Voltage	V _{IN}	5.0 V
Output Voltage	Vout	1.2 V
Switching Frequency	f _{SW}	2.2 MHz (Typ)
Output Capacitor	Соит	44 µF
Soft Start Setting Time	tss_ext	6.0 ms (Typ)
Maximum Output Current	IOUTMAX	3 A

1. Application Example

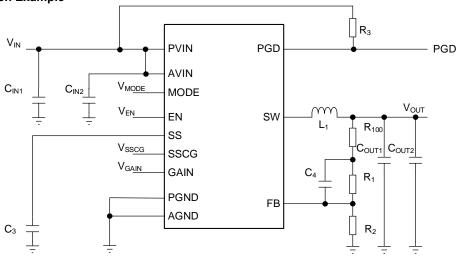


Figure 40. Application Circuit

2. Switching Frequency

The switching frequency fsw is fixed at 2.2 MHz (Typ) inside the IC.

3. Output Voltage Setting

The output voltage value can be set by the feedback resistance ratio.

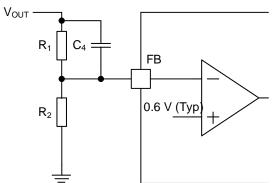


Figure 41. Feedback Resistor Circuit

$$V_{OUT} = \frac{R_1 + R_2}{R_2} \times 0.6 \text{ [V]}$$

SW Minimum ON Time that BD9S303MUF-C can output stably in the entire load range is 50 ns. Use this value to calculate the input and output conditions that satisfy the following equation.

$$50 [ns] \le \frac{V_{OUT}}{V_{IN} \times f_{SW}}$$

Table 2	Configuration	Pacietore	and	Canacitor
Table 7.	Commonation	Designos	ann	Cabaciloi

Output Voltage V _{OUT}	R ₁	R ₂	C ₄
0.8 V	10 kΩ	30 kΩ	22 pF
0.9 V	10 kΩ	20 kΩ	22 pF
1.0 V	10 kΩ	15 kΩ	22 pF
1.2 V	47 kΩ	47 kΩ	22 pF
1.5 V	33 kΩ	22 kΩ	33 pF
1.8 V	30 kΩ	15 kΩ	47 pF
2.5 V	51 kΩ	16 kΩ	33 pF
3.3 V	68 kΩ	15 kΩ	22 pF

Selection of Components Externally Connected - continued

4. Selection of Input Capacitor

The input capacitor requires a large capacitance value for C_{IN1} and a small capacitance value for C_{IN2} . Use ceramic type capacitor for these capacitors. C_{IN1} is used to suppress the ripple noise, and C_{IN2} is used to suppress the switching noise. These ceramic capacitors are effective by being placed as close as possible to the PVIN pin and the AVIN pin. The effective capacitance value 4.7 μ F or more for C_{IN1} , and 0.06 μ F or more for C_{IN2} are necessary. In addition, the voltage rating for both capacitors has to be twice the typical input voltage. Set the capacitance value so that it does not fall to its minimum required value against the capacitance value variances, temperature characteristics, DC bias characteristics, aging characteristics, and etc. Use components which are comparatively same with the components used in "Selection of Components Externally Connected". Moreover, factors like the PCB layout and the position of the capacitor may lead to IC malfunction. Refer to "PCB layout Design".

5. Selection of Output LC Filter

The inductor in the DC/DC converter supplies a continuous current to the load and functions as a filter to smooth the output voltage. When a large inductor is selected, the Inductor ripple current ΔI_L and the output voltage ripple ΔV_{P-P} are reduced. It is the trade-off between the size and the cost of the inductor. Select a nominal inductance value between 0.33 μ H and 0.68 μ H. When using the Light Load Mode (LLM) control, it is recommended to use 0.33 μ H or 0.47 μ H in the condition where the input voltage V_{IN} is more than 4 V. Also, it is recommended to use 0.33 μ H under the condition of 4 V or less.

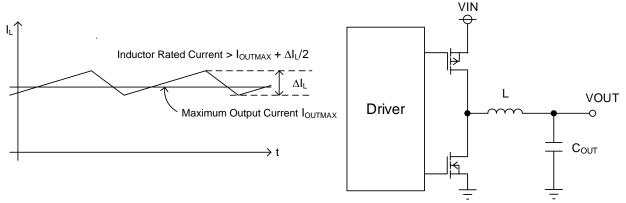


Figure 42. Waveform of Current through Inductor

Figure 43. Output LC Filter Circuit

Inductor ripple current ΔI_{L} can be represented by the following equation.

$$\Delta I_L = V_{OUT} \times (V_{IN} - V_{OUT}) \times \frac{1}{V_{IN} \times f_{SW} \times L_1} = 882 \text{ [mA]}$$

where

 V_{IN} is the 5.0 V V_{OUT} is the 1.2 V L_1 is the 0.47 $\mu {\rm H}$

 f_{SW} is the 2.2 MHz (Switching Frequency)

The rated current of the inductor must be larger than the sum of the maximum output current and 1/2 of the inductor ripple current ΔI_L .

Table 3. List of Inductors

Manufacturer	Inductor Series	Inductance	DCR	I_{TEMP}	WxLxH
Manufacturer	inductor Series	[µH]	[mΩ]	[A]	[mm]
TDK	SPM5030VT	0.33	4.2	14.2	5.1 x 5.3 x 3.0
TDK	SPM5030VT	0.47	5.4	12.9	5.1 x 5.3 x 3.0
TDK	SPM5030VT	0.68	7.4	10.7	5.1 x 5.3 x 3.0
TDK	TFM252012ALMA	0.33	13.0	7.8	2.5 x 2.0 x 1.2
TDK	TFM252012ALMA	0.47	19.0	6.5	2.5 x 2.0 x 1.2
Panasonic	ETQP3M	0.47	5.8	11.6	5.5 x 5.0 x 3.0
Panasonic	ETQP3M	0.68	7.6	10.2	5.5 x 5.0 x 3.0
Coilcraft	XGL4020	0.33	3.0	23.0	4.0 x 4.0 x 2.1
Coilcraft	XGL4020	0.47	4.2	19.7	4.0 x 4.0 x 2.1

5. Selection of Output LC Filter - continued

The output capacitor C_{OUT} affects the output ripple voltage characteristics. C_{OUT} must satisfy the required ripple voltage characteristics. The output ripple voltage can be represented by the following equation.

$$\Delta V_{RPL} = \Delta I_L \times \left(R_{ESR} + \frac{1}{8 \times C_{OUT} \times f_{SW}} \right) [V]$$

where

 $R_{\it ESR}$ is the Equivalent Series Resistance (ESR) of the output capacitor.

$$\Delta V_{RPL} = 0.882 \times \left(10 \times 10^{-3} + \frac{1}{8 \times 44 \times 2.2}\right) = 9.96 \text{ [mV]}$$

where

 C_{OUT} is the 44 μF R_{ESR} is the 10 $m\Omega$

If the total value of all capacitors connected to V_{OUT} is large, the inrush current at startup may cause the over current protection to operate and the output may not start. In this case, set the soft start time to satisfy the following equation.

$$t_{SS} > \frac{V_{OUT} \times C_{OUT(TOTAL)}}{(I_{OCPH(MIN)} - I_{SWSTART(MAX)})}$$
 [s]

where:

 $C_{OUT(TOTAL)}$ is the total value of all capacitors connected to Vout [F] $I_{SWSTART(MAX)}$ is the maximum output load current expected at startup [A]

 $I_{OCPH(MIN)}$ is the minimum OCP operation SW current 3.6 [A]

 t_{SS} is the Soft Start Time [s] V_{OUT} is the Output voltage [V]

In case of large changing input voltage and output current, select the capacitance value accordingly by verifying that the actual application setup meets the required specification.

6. Selection of Soft Start Capacitor

Turning the EN pin High activates the soft start function. This causes the output voltage to rise gradually while the current at startup is placed under control. This allows the prevention of output voltage overshoot and inrush current. The rise time t_{SS_EXT} depends on the value of the capacitor connected to the SS pin. The capacitance value should be set in the range between 3300 pF and 0.1 μ F.

$$t_{SS_EXT} = \frac{(C_3 \times V_{FB})}{I_{SS}} [s]$$

where

 $t_{SS\ EXT}$ is the Soft Start Setting Time

 \mathcal{C}_3 is the Capacitor connected to the SS pin

 V_{FB} is the FB pin Voltage 0.6 V (Typ)

 I_{SS} is the SS Charge Current 1.0 μ A (Typ)

With $C_3 = 0.01 \mu F$

$$t_{SS_EXT} = \frac{(0.01 \times 0.6)}{1.0} = 6.0$$
 [ms]

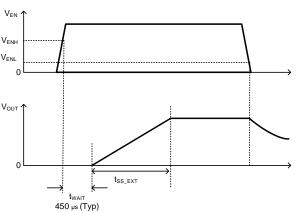


Figure 44. Soft Start Timing Chart

Turning the EN pin High without connecting capacitor to the SS pin and keeping the SS pin either OPEN condition or $10 \text{ k}\Omega$ to $100 \text{ k}\Omega$ pull up condition to power supply, the output rises in $t_{SS} = 0.8 \text{ ms}$ (Typ).

Selection of Components Externally Connected - continued

7. Input Voltage Startup

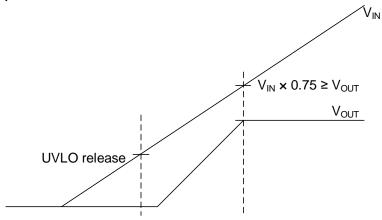


Figure 45. Input Voltage Startup Time

The soft start function starts up the device according to the specified soft start time. After UVLO is released, the voltage range that can be outputted during the soft start operation is 75 % or less of the input voltage. Note that the input voltage during the startup with soft start should satisfy the following expression.

$$V_{IN} \ge \frac{V_{OUT}}{0.75} [V]$$

Recommended Parts Manufacturer List

Shown below is the list of the recommended parts manufacturers for reference.

Device	Туре	Manufacturer	URL
С	Ceramic capacitors	Murata	www.murata.com
С	Ceramic capacitors	TDK	www.tdk.com
L	Inductors	Coilcraft	www.coilcraft.com
L	Inductors	Cyntec	www.cyntec.com
L	Inductors	Murata	www.murata.com
L	Inductors	Sumida	www.sumida.com
L	Inductors	TDK	www.tdk.com
R	Resistors	ROHM	www.rohm.com

Table 4. Recommended Parts Manufacturers

Application Characteristic Data (Reference Data) Measurement Circuit

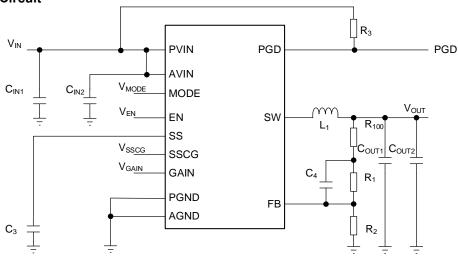


Figure 46. Measurement Schematic

Table 5. List of Components for The Fast Load Response Mode (Note 1) (GAIN = High)

NO	Package	Parameter	Part Name	Туре	Manufacture	
L ₁	_	0.47 μH (V _{IN} = 5.0 V)	SPM5030VT-R47M-D	Inductor	TDK	
<u>-</u> ,		$0.33 \mu H (V_{IN} = 3.3 V)$	SPM5030VT-R33M-D	madotor		
C _{OUT1}	3216	22 μF, X7R, 6.3 V	GCM31CR70J226KE26	Ceramic Capacitor	Murata	
C _{OUT2}	3216	22 μF, X7R, 6.3 V	GCM31CR70J226KE26	Ceramic Capacitor	Murata	
C _{IN1}	2012	10 μF, X7R, 10 V	GCM21BR71A106KE21	Ceramic Capacitor	Murata	
C _{IN2}	1005	0.1 μF , X7R, 16 V	GCM155R71C104KA55	Ceramic Capacitor	Murata	
R ₁₀₀	-	SHORT	-	-	-	
R ₁	1005	Depending on V _{OUT} (Note 2)	MCR01MZPF Series	Chip Resistor	ROHM	
R_2	1005	Depending on V _{OUT} (Note 2)	MCR01MZPF Series	Chip Resistor	ROHM	
R ₃	1005	100 kΩ, 1 %, 1/16 W	MCR01MZPF Series	Chip Resistor	ROHM	
C ₃	OPEN	-	-	-	-	
C ₄	1005	Depending on V _{OUT} (Note 2)	GCM1555C1H Series	Ceramic Capacitor	Murata	
GAIN	-	High	-	-	-	

Table 6. List of Components for The Low Output Capacitance Mode (Note 1) (GAIN = Low)

NO	Package	Parameter	Part Name	Туре	Manufacture
L ₁	-	0.47 μH (V _{IN} = 5.0 V) 0.33 μH (V _{IN} = 3.3 V)	SPM5030VT-R47M-D SPM5030VT-R33M-D	Inductor	TDK
C _{OUT1}	3216	22 μF, X7R, 6.3 V	GCM31CR70J226KE26	Ceramic Capacitor	Murata
Соит2	OPEN	-	-	-	-
C _{IN1}	2012	10 μF, X7R, 10 V	GCM21BR71A106KE21	Ceramic Capacitor	Murata
C _{IN2}	1005	0.1 μF , X7R, 16 V	GCM155R71C104KA55	Ceramic Capacitor	Murata
R ₁₀₀	-	SHORT	•	-	1
R ₁	1005	Depending on V _{OUT} (Note 2)	MCR01MZPF Series	Chip Resistor	ROHM
R ₂	1005	Depending on V _{OUT} (Note 2)	MCR01MZPF Series	Chip Resistor	ROHM
R ₃	1005	100 kΩ, 1 %, 1/16 W	MCR01MZPF Series	Chip Resistor	ROHM
C ₃	OPEN	-		-	-
C ₄	1005	Depending on V _{OUT} (Note 2)	GCM1555C1H Series	Ceramic Capacitor	Murata
GAIN	-	Low	-	-	-

(Note 1) For more information on each mode, see Function Explanations <u>6. Error Amplifier Gain Switching Function</u>. (Note 2) For the part parameters, see Selection of Components Externally Connected <u>3. Output Voltage Setting</u>.

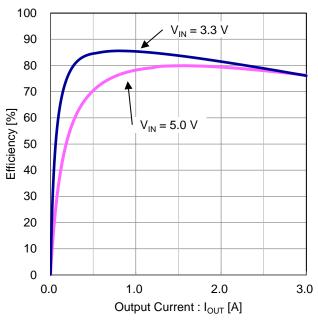


Figure 47. Efficiency vs Output Current (V_{OUT} = 1.0 V, MODE = High)

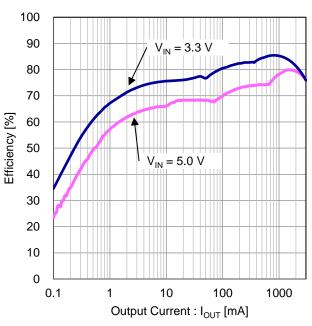


Figure 48. Efficiency vs Output Current (V_{OUT} = 1.0 V, MODE = Low)

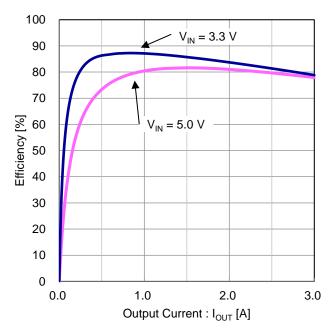


Figure 49. Efficiency vs Output Current ($V_{OUT} = 1.2 \text{ V}$, MODE = High)

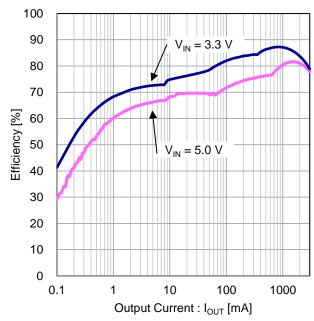


Figure 50. Efficiency vs Output Current (V_{OUT} = 1.2 V, MODE = Low)

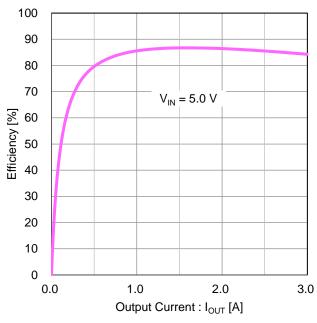


Figure 51. Efficiency vs Output Current (V_{OUT} = 1.8 V, MODE = High)

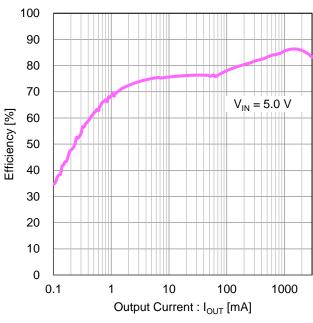


Figure 52. Efficiency vs Output Current (V_{OUT} = 1.8 V, MODE = Low)

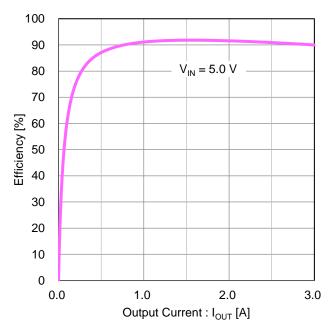


Figure 53. Efficiency vs Output Current ($V_{OUT} = 3.3 \text{ V}, \text{MODE} = \text{High}$)

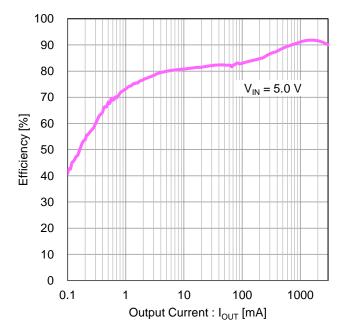


Figure 54. Efficiency vs Output Current (V_{OUT} = 3.3 V, MODE = Low)

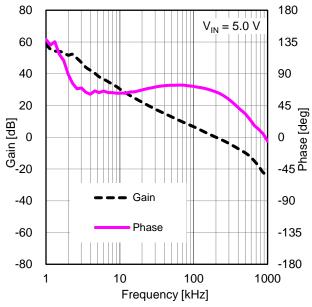


Figure 55. Frequency Characteristics (V_{OUT} = 1.0 V, GAIN = High, I_{OUT} = 1.5 A)

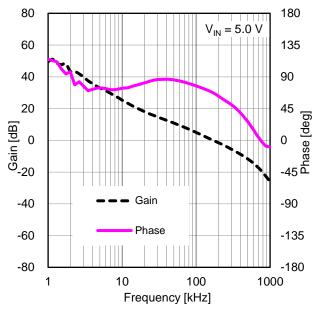


Figure 56. Frequency Characteristics (V_{OUT} = 1.0 V, GAIN = Low, I_{OUT} = 1.5 A)

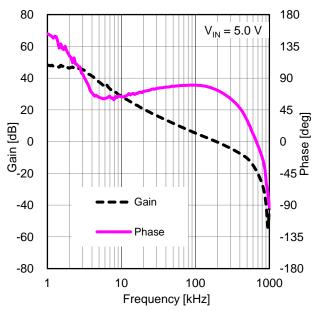


Figure 57. Frequency Characteristics (V_{OUT} = 1.2 V, GAIN = High, I_{OUT} = 1.5 A)

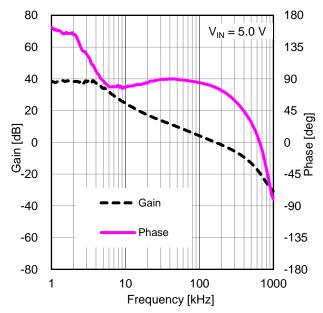


Figure 58. Frequency Characteristics (V_{OUT} = 1.2 V, GAIN = Low, I_{OUT} = 1.5 A)

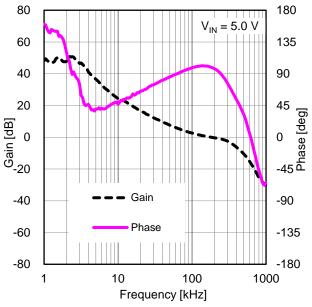


Figure 59. Frequency Characteristics (V_{OUT} = 1.8 V, GAIN = High, I_{OUT} = 1.5 A)

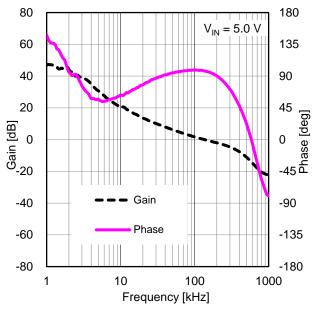


Figure 60. Frequency Characteristics (V_{OUT} = 1.8 V, GAIN = Low, I_{OUT} = 1.5 A)

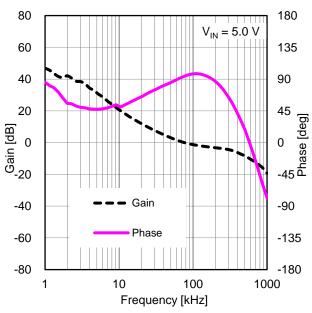


Figure 61. Frequency Characteristics (V_{OUT} = 3.3 V, GAIN = High, I_{OUT} = 1.5 A)

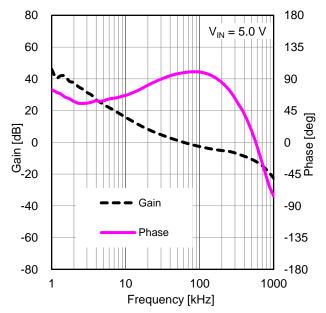


Figure 62. Frequency Characteristics (V_{OUT} = 3.3 V, GAIN = Low, I_{OUT} = 1.5 A)

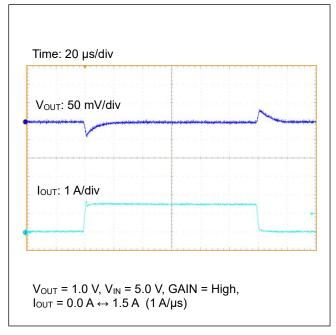


Figure 63. Load Transient Response (V_{OUT} = 1.0 V, GAIN = High)

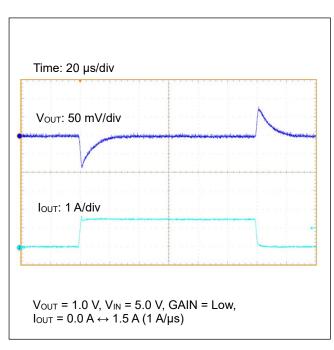


Figure 64. Load Transient Response (V_{OUT} = 1.0 V, GAIN = Low)

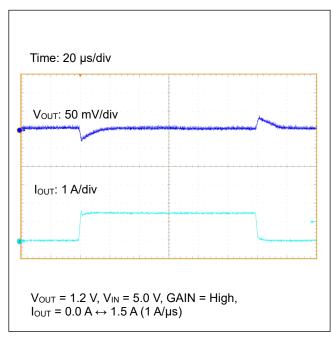


Figure 65. Load Transient Response (V_{OUT} = 1.2 V, GAIN = High)

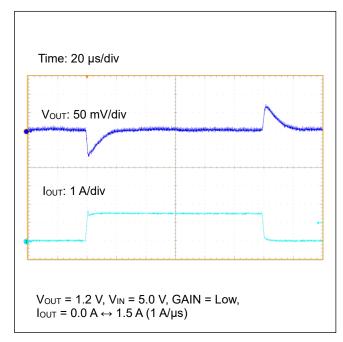


Figure 66. Load Transient Response (Vout = 1.2 V, GAIN = Low)

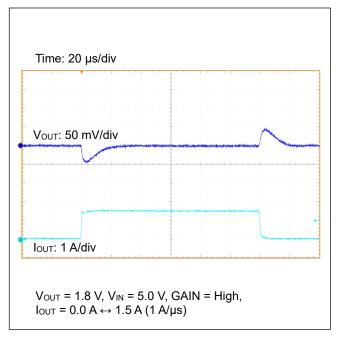


Figure 67. Load Transient Response (V_{OUT} = 1.8 V, GAIN = High)

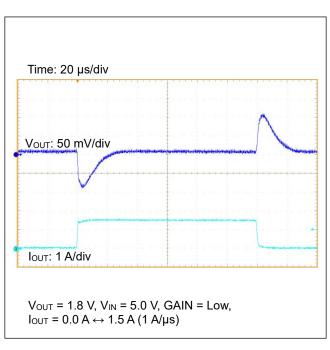


Figure 68. Load Transient Response (V_{OUT} = 1.8 V, GAIN = Low)

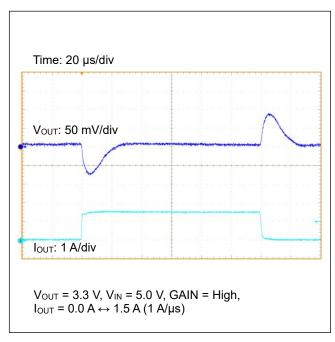


Figure 69. Load Transient Response (Vout = 3.3 V, GAIN = High)

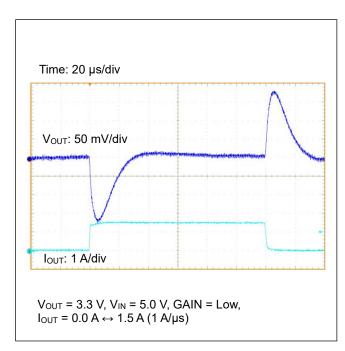


Figure 70. Load Transient Response (Vout = 3.3 V, GAIN = Low)

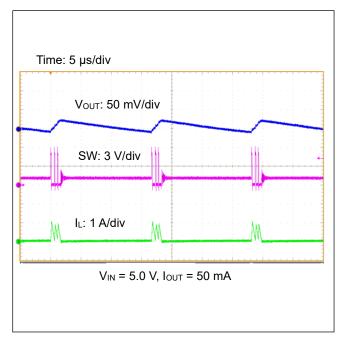


Figure 71. Ripple Voltage (V_{OUT} = 1.0 V, LLM)

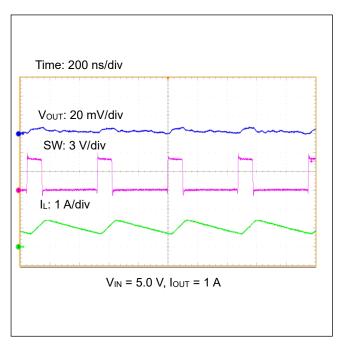


Figure 72. Ripple Voltage (Vout = 1.0 V, PWM)

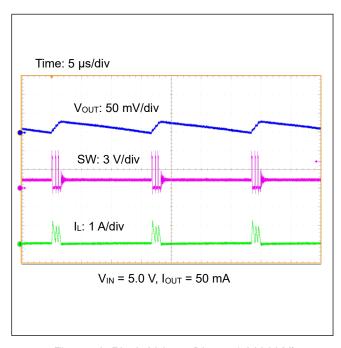


Figure 73. Ripple Voltage (V_{OUT} = 1.2 V, LLM)

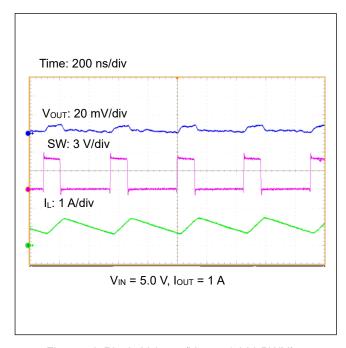


Figure 74. Ripple Voltage (V_{OUT} = 1.2 V, PWM)

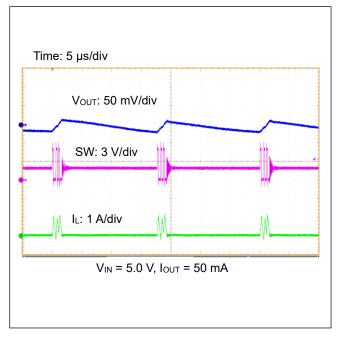


Figure 75. Ripple Voltage (V_{OUT} = 1.8 V, LLM)

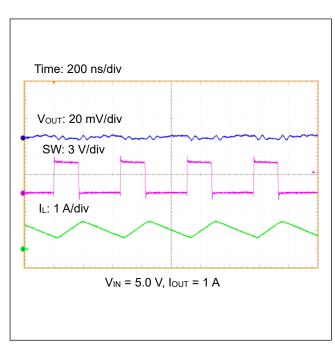


Figure 76. Ripple Voltage (Vout = 1.8 V, PWM)

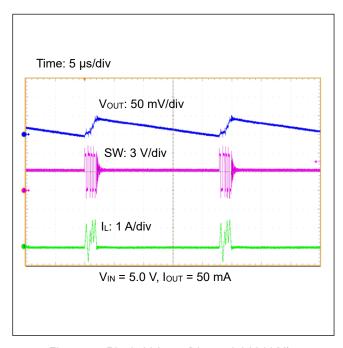


Figure 77. Ripple Voltage (V_{OUT} = 3.3 V, LLM)

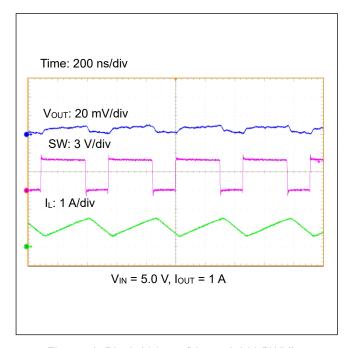


Figure 78. Ripple Voltage (V_{OUT} = 3.3 V, PWM)

PCB Layout Design

PCB layout design for DC/DC converter is very important. Appropriate layout can avoid various problems concerning power supply circuit. Figure 79 to 81 show the current path in a buck DC/DC converter circuit. The Loop 1 in Figure 79 is a current path when High Side Switch is ON and Low Side Switch is OFF, the Loop 2 in Figure 80 is when High Side Switch is OFF and Low Side Switch is ON. The thick line in Figure 81 shows the difference between Loop1 and Loop2. The current in thick line change sharply each time the switching element High Side and Low Side Switch change from OFF to ON, and vice versa. These sharp changes induce a waveform with harmonics in this loop. Therefore, the loop area of thick line that is consisted by input capacitor and IC should be as small as possible to minimize noise. For more details, refer to application note of switching regulator series "PCB Layout Techniques of Buck Converter".

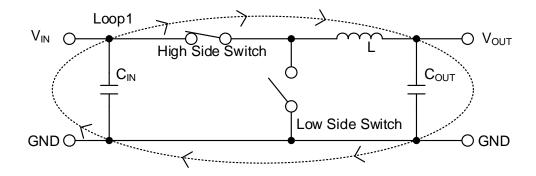


Figure 79. Current Path when High Side Switch = ON, Low Side Switch = OFF

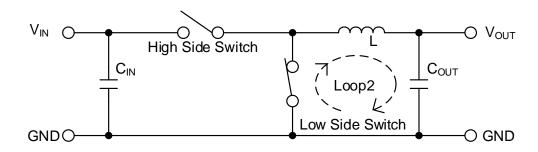


Figure 80. Current Path when High Side Switch = OFF, Low Side Switch = ON

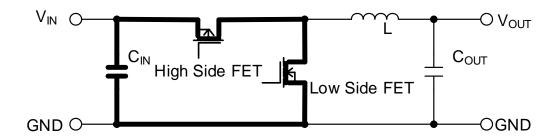
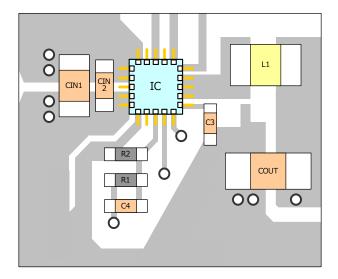


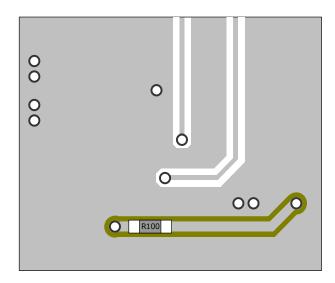
Figure 81. Difference of Current and Critical Area in Layout

PCB Layout Design - continued

When designing the PCB layout, Pay extra attention to the following points.

- Connect the input capacitor C_{IN} as close as possible to the PVIN pin on the same plane as the IC.
- Switching nodes such as SW are susceptible to noise due to AC coupling with other nodes. Route the inductor pattern as thick and as short as possible.
- R₁ and R₂ shall be located as close as possible to the FB pin and the wiring between R₁ and R₂ to the FB pin shall be as short as possible.
- Provide line connected to FB far from the SW nodes.
- Influence from the switching noise can be minimized, by isolating Power (Input and Output Capacitor) GND and Reference (FB) GND.
- R₁₀₀ is provided for the measurement of feedback frequency characteristics (optional). By inserting a resistor into R₁₀₀, it is possible to measure the frequency characteristics of feedback (phase margin) using FRA etc. R₁₀₀ is short-circuited for normal use.





Example of Evaluation Board Layout (Top View)

Example of Evaluation Board Layout (Bottom View)

Figure 82. Example of Evaluation Board Layout

Power Dissipation

For thermal design, be sure to operate the IC within the following conditions. (Since the temperatures described hereunder are all guaranteed temperatures, take margin into account.)

- 1. The ambient temperature Ta is to be 125 °C or less.
- 2. The chip junction temperature Tj is to be 150 °C or less.

The chip junction temperature Tj can be considered in the following two patterns:

1. To obtain Tj from the package surface center temperature Tt in actual use

$$Tj = Tt + \psi_{IT} \times W$$
 [°C]

2. To obtain Tj from the ambient temperature Ta

$$Tj = Ta + \theta_{IA} \times W$$
 [°C]

where

 ψ_{IT} is junction to top characterization parameter (<u>Thermal Resistance</u>)

 $heta_{IA}$ is junction to ambient (<u>Thermal Resistance</u>)

The heat loss W of the IC can be obtained by the formula shown below:

$$W = R_{ONH} \times {I_{OUT}}^2 \times \frac{V_{OUT}}{V_{IN}} + R_{ONL} \times {I_{OUT}}^2 \left(1 - \frac{V_{OUT}}{V_{IN}}\right)$$
$$+V_{IN} \times I_{CC} + \frac{1}{2} \times (tr + tf) \times V_{IN} \times I_{OUT} \times f_{SW} \text{ [W]}$$

where:

 R_{ONH} is the High Side FET ON Resistance (<u>Electrical Characteristics</u>) [Ω]

 R_{ONL} is the Low Side FET ON Resistance (<u>Electrical Characteristics</u>) [Ω]

 I_{OUT} is the Output Current [A] V_{OUT} is the Output Voltage [V] V_{IN} is the Input Voltage [V]

 I_{CC} is the Circuit Current (<u>Electrical Characteristics</u>) [A]

tr is the Switching Rise Time [s] (Typ: 2 ns) tf is the Switching Fall Time [s] (Typ: 2 ns)

 f_{SW} is the Switching Frequency (<u>Electrical Characteristics</u>) [Hz]

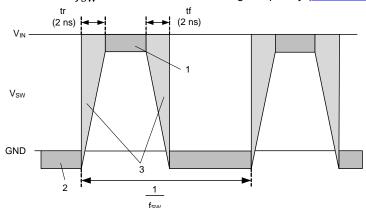


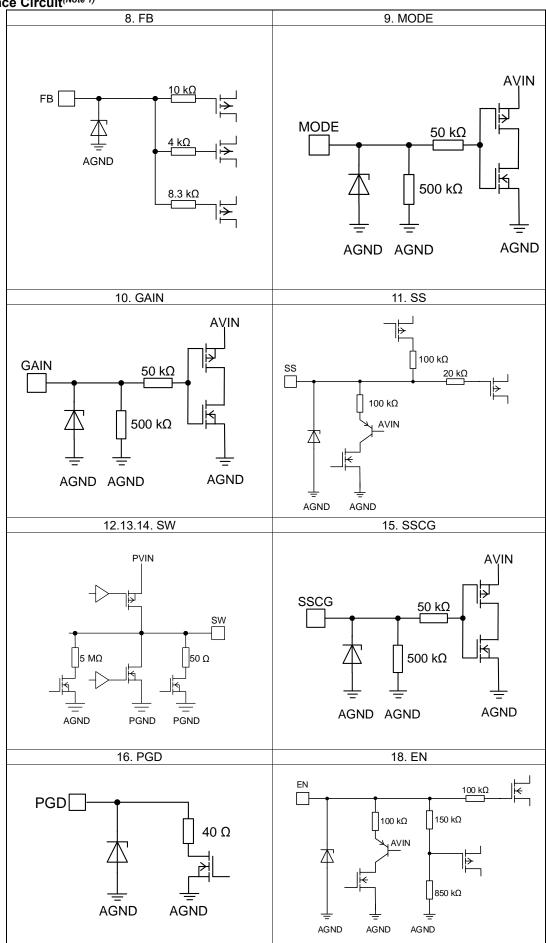
Figure 83. SW Waveform

1.
$$R_{ONH} \times I_{OUT}^2$$

2.
$$R_{ONL} \times I_{OUT}^2$$

3.
$$\frac{1}{2} \times (tr + tf) \times V_{IN} \times I_{OUT} \times f_{SW}$$

I/O Equivalence Circuit^(Note 1)



(Note 1) Resistance value is typical.

Operational Notes

1. Reverse Connection of Power Supply

Connecting the power supply in reverse polarity can damage the IC. Take precautions against reverse polarity when connecting the power supply, such as mounting an external diode between the power supply and the IC's power supply pins.

2. Power Supply Lines

Design the PCB layout pattern to provide low impedance supply lines. Furthermore, connect a capacitor to ground at all power supply pins. Consider the effect of temperature and aging on the capacitance value when using electrolytic capacitors.

3. Ground Voltage

Ensure that no pins are at a voltage below that of the ground pin at any time, even during transient condition. However, pins that drive inductive loads (e.g. motor driver outputs, DC-DC converter outputs) may inevitably go below ground due to back EMF or electromotive force. In such cases, the user should make sure that such voltages going below ground will not cause the IC and the system to malfunction by examining carefully all relevant factors and conditions such as motor characteristics, supply voltage, operating frequency and PCB wiring to name a few.

4. Ground Wiring Pattern

When using both small-signal and large-current ground traces, the two ground traces should be routed separately but connected to a single ground at the reference point of the application board to avoid fluctuations in the small-signal ground caused by large currents. Also ensure that the ground traces of external components do not cause variations on the ground voltage. The ground lines must be as short and thick as possible to reduce line impedance.

5. Recommended Operating Conditions

The function and operation of the IC are guaranteed within the range specified by the recommended operating conditions. The characteristic values are guaranteed only under the conditions of each item specified by the electrical characteristics.

6. Inrush Current

When power is first supplied to the IC, it is possible that the internal logic may be unstable and inrush current may flow instantaneously due to the internal powering sequence and delays, especially if the IC has more than one power supply. Therefore, give special consideration to power coupling capacitance, power wiring, width of ground wiring, and routing of connections.

7. Testing on Application Boards

When testing the IC on an application board, connecting a capacitor directly to a low-impedance output pin may subject the IC to stress. Always discharge capacitors completely after each process or step. The IC's power supply should always be turned off completely before connecting or removing it from the test setup during the inspection process. To prevent damage from static discharge, ground the IC during assembly and use similar precautions during transport and storage.

8. Inter-pin Short and Mounting Errors

Ensure that the direction and position are correct when mounting the IC on the PCB. Incorrect mounting may result in damaging the IC. Avoid nearby pins being shorted to each other especially to ground, power supply and output pin. Inter-pin shorts could be due to many reasons such as metal particles, water droplets (in very humid environment) and unintentional solder bridge deposited in between pins during assembly to name a few.

9. Unused Input Pins

Input pins of an IC are often connected to the gate of a MOS transistor. The gate has extremely high impedance and extremely low capacitance. If left unconnected, the electric field from the outside can easily charge it. The small charge acquired in this way is enough to produce a significant effect on the conduction through the transistor and cause unexpected operation of the IC. So unless otherwise specified, unused input pins should be connected to the power supply or ground line.

Operational Notes - continued

10. Regarding the Input Pin of the IC

This monolithic IC contains P+ isolation and P substrate layers between adjacent elements in order to keep them isolated. P-N junctions are formed at the intersection of the P layers with the N layers of other elements, creating a parasitic diode or transistor. For example (refer to figure below):

When GND > Pin A and GND > Pin B, the P-N junction operates as a parasitic diode. When GND > Pin B, the P-N junction operates as a parasitic transistor.

Parasitic diodes inevitably occur in the structure of the IC. The operation of parasitic diodes can result in mutual interference among circuits, operational faults, or physical damage. Therefore, conditions that cause these diodes to operate, such as applying a voltage lower than the GND voltage to an input pin (and thus to the P substrate) should be avoided.

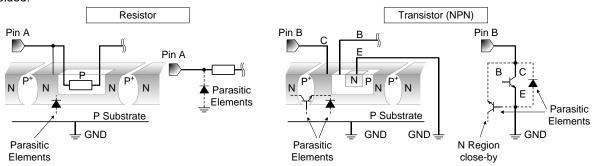


Figure 84. Example of Monolithic IC Structure

11. Ceramic Capacitor

When using a ceramic capacitor, determine a capacitance value considering the change of capacitance with temperature and the decrease in nominal capacitance due to DC bias and others.

12. Thermal Shutdown Circuit (TSD)

This IC has a built-in thermal shutdown circuit that prevents heat damage to the IC. Normal operation should always be within the IC's maximum junction temperature rating. If however the rating is exceeded for a continued period, the junction temperature (Tj) will rise which will activate the TSD circuit that will turn OFF power output pins. When the Tj falls below the TSD threshold, the circuits are automatically restored to normal operation.

Note that the TSD circuit operates in a situation that exceeds the absolute maximum ratings and therefore, under no circumstances, should the TSD circuit be used in a set design or for any purpose other than protecting the IC from heat damage.

13. Over Current Protection Circuit (OCP)

This IC incorporates an integrated overcurrent protection circuit that is activated when the load is shorted. This protection circuit is effective in preventing damage due to sudden and unexpected incidents. However, the IC should not be used in applications characterized by continuous operation or transitioning of the protection circuit.

14. Functional Safety

"ISO 26262 Process Compliant to Support ASIL-*"

A product that has been developed based on an ISO 26262 design process compliant to the ASIL level described in the datasheet.

"Safety Mechanism is Implemented to Support Functional Safety (ASIL-*)"

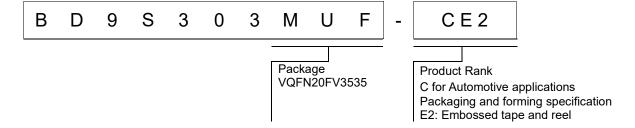
A product that has implemented safety mechanism to meet ASIL level requirements described in the datasheet.

"Functional Safety Supportive Automotive Products"

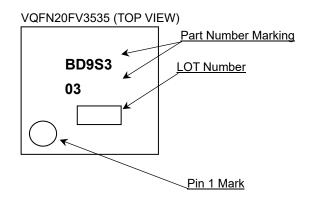
A product that has been developed for automotive use and is capable of supporting safety analysis with regard to the functional safety.

Note: "ASIL-*" is stands for the ratings of "ASIL-A", "-B", "-C" or "-D" specified by each product's datasheet

Ordering Information



Marking Diagram



Physical Dimension and Packing Information VQFN20FV3535 Package Name 3. 5 ± 0 . 1 5 ± 0 . 1PIN MARK 0 MAX 0 2 +0. 0 □ 0. 08 S 0) 2. 05 ± 0.1 C0. 2 $\overline{\mathsf{U}}$ 20 $0.4\pm0.$ 2 16 \cap \cap \cap \cap 0.75 $0.25_{\,-0.04}^{\,+0.05}$ 0. 5 (UNIT:mm) PKG: VQFN20FV3535 Drawing No. EX375-5001-4 NOTE: Dimensions in () for reference only. < Tape and Reel Information > Таре Embossed carrier tape Quantity 2500pcs Direction of feed The direction is the pin 1 of product is at the upper left when you hold reel on the left hand and you pull out the tape on the right hand 0 0 \circ 0 0 0 0 0 0 0 0 E2 TR E2 TR E2 TR E2 TR E2 TR E2 TR TL E1 TL E1 TL E1 TL E1 TL E1 TL E1 Direction of feed Pocket Quadrants

Reel

Revision History

Date	Revision	Changes
15.Jun.2023	001	New Release

Notice

Precaution on using ROHM Products

1. If you intend to use our Products in devices requiring extremely high reliability (such as medical equipment (Note 1), aircraft/spacecraft, nuclear power controllers, etc.) and whose malfunction or failure may cause loss of human life, bodily injury or serious damage to property ("Specific Applications"), please consult with the ROHM sales representative in advance. Unless otherwise agreed in writing by ROHM in advance, ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of any ROHM's Products for Specific Applications.

(Note1) Medical Equipment Classification of the Specific Applications

JÁPAN	USA	EU	CHINA
CLASSIII	CL ACCIII	CLASS II b	CL ACCIII
CLASSIV	CLASSⅢ	CLASSIII	CLASSⅢ

- 2. ROHM designs and manufactures its Products subject to strict quality control system. However, semiconductor products can fail or malfunction at a certain rate. Please be sure to implement, at your own responsibilities, adequate safety measures including but not limited to fail-safe design against the physical injury, damage to any property, which a failure or malfunction of our Products may cause. The following are examples of safety measures:
 - [a] Installation of protection circuits or other protective devices to improve system safety
 - [b] Installation of redundant circuits to reduce the impact of single or multiple circuit failure
- 3. Our Products are not designed under any special or extraordinary environments or conditions, as exemplified below. Accordingly, ROHM shall not be in any way responsible or liable for any damages, expenses or losses arising from the use of any ROHM's Products under any special or extraordinary environments or conditions. If you intend to use our Products under any special or extraordinary environments or conditions (as exemplified below), your independent verification and confirmation of product performance, reliability, etc, prior to use, must be necessary:
 - [a] Use of our Products in any types of liquid, including water, oils, chemicals, and organic solvents
 - [b] Use of our Products outdoors or in places where the Products are exposed to direct sunlight or dust
 - [c] Use of our Products in places where the Products are exposed to sea wind or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [d] Use of our Products in places where the Products are exposed to static electricity or electromagnetic waves
 - [e] Use of our Products in proximity to heat-producing components, plastic cords, or other flammable items
 - [f] Sealing or coating our Products with resin or other coating materials
 - [g] Use of our Products without cleaning residue of flux (Exclude cases where no-clean type fluxes is used. However, recommend sufficiently about the residue.); or Washing our Products by using water or water-soluble cleaning agents for cleaning residue after soldering
 - [h] Use of the Products in places subject to dew condensation
- 4. The Products are not subject to radiation-proof design.
- 5. Please verify and confirm characteristics of the final or mounted products in using the Products.
- 6. In particular, if a transient load (a large amount of load applied in a short period of time, such as pulse, is applied, confirmation of performance characteristics after on-board mounting is strongly recommended. Avoid applying power exceeding normal rated power; exceeding the power rating under steady-state loading condition may negatively affect product performance and reliability.
- 7. De-rate Power Dissipation depending on ambient temperature. When used in sealed area, confirm that it is the use in the range that does not exceed the maximum junction temperature.
- 8. Confirm that operation temperature is within the specified range described in the product specification.
- 9. ROHM shall not be in any way responsible or liable for failure induced under deviant condition from what is defined in this document.

Precaution for Mounting / Circuit board design

- 1. When a highly active halogenous (chlorine, bromine, etc.) flux is used, the residue of flux may negatively affect product performance and reliability.
- 2. In principle, the reflow soldering method must be used on a surface-mount products, the flow soldering method must be used on a through hole mount products. If the flow soldering method is preferred on a surface-mount products, please consult with the ROHM representative in advance.

For details, please refer to ROHM Mounting specification

Precautions Regarding Application Examples and External Circuits

- 1. If change is made to the constant of an external circuit, please allow a sufficient margin considering variations of the characteristics of the Products and external components, including transient characteristics, as well as static characteristics.
- 2. You agree that application notes, reference designs, and associated data and information contained in this document are presented only as guidance for Products use. Therefore, in case you use such information, you are solely responsible for it and you must exercise your own independent verification and judgment in the use of such information contained in this document. ROHM shall not be in any way responsible or liable for any damages, expenses or losses incurred by you or third parties arising from the use of such information.

Precaution for Electrostatic

This Product is electrostatic sensitive product, which may be damaged due to electrostatic discharge. Please take proper caution in your manufacturing process and storage so that voltage exceeding the Products maximum rating will not be applied to Products. Please take special care under dry condition (e.g. Grounding of human body / equipment / solder iron, isolation from charged objects, setting of lonizer, friction prevention and temperature / humidity control).

Precaution for Storage / Transportation

- 1. Product performance and soldered connections may deteriorate if the Products are stored in the places where:
 - [a] the Products are exposed to sea winds or corrosive gases, including Cl₂, H₂S, NH₃, SO₂, and NO₂
 - [b] the temperature or humidity exceeds those recommended by ROHM
 - [c] the Products are exposed to direct sunshine or condensation
 - [d] the Products are exposed to high Electrostatic
- Even under ROHM recommended storage condition, solderability of products out of recommended storage time period
 may be degraded. It is strongly recommended to confirm solderability before using Products of which storage time is
 exceeding the recommended storage time period.
- 3. Store / transport cartons in the correct direction, which is indicated on a carton with a symbol. Otherwise bent leads may occur due to excessive stress applied when dropping of a carton.
- 4. Use Products within the specified time after opening a humidity barrier bag. Baking is required before using Products of which storage time is exceeding the recommended storage time period.

Precaution for Product Label

A two-dimensional barcode printed on ROHM Products label is for ROHM's internal use only.

Precaution for Disposition

When disposing Products please dispose them properly using an authorized industry waste company.

Precaution for Foreign Exchange and Foreign Trade act

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